#### SILICON (Si) POWER MOSFET ▲ CEM6822



# **CEM6822**

# 60V ▲ 82mΩ ▲ 3.6A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability

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Parameter ( $T_A = 25^{\circ}C$ , unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	60V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current	I <sub>D</sub>	3.6A
Pulsed Drain Current Note 1	I <sub>DM</sub>	14.4A
Maximum Power Dissipation	PD	2.5W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

#### **THERMAL CHARACTERISTICS**

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>th_ja</sub>	50°C/W

#### **APPLICATIONS**

Audio	DC	DC/DC	Industrial	Load
Amplifier	Fan	Converter	Control	Switches
<b>(</b> )	$\bigcirc$			

## **PIN DESCRIPTION**

Circuit Diagram	Outline - Top View	Pin No.	Description
D (5,6,7,8)	8 7 6 5 <u><u><u></u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u><u></u></u>	1 2 3 4	Source Source Source Gate
S (1,2,3)		5 6 7 8	Drain Drain Drain Drain

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## **ELECTRICAL CHARACTERISTICS A T**<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	BV <sub>DSS</sub>	60			V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	V <sub>GS(th)</sub>	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 2A$	R <sub>DS(ON)</sub>		82	105	mΩ
Static Drain-Source On-Resistance	$V_{GS}$ = 4.5V, I <sub>D</sub> = 1A	R <sub>DS(ON)</sub>		92	130	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = 30V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		405		рF
Output Capacitance	$V_{DS}$ = 30V, $V_{GS}$ = 0V, f = 1MHz	Coss		70		рF
Reverse Transfer Capacitance	$V_{DS}$ = 30V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		30		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1.5A, $R_{\text{G(ext)}}$ = 3 $\Omega$	t <sub>D(ON)</sub>		7		ns
Turn-On Rise Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1.5A, $R_{\text{G(ext)}}$ = 3 $\Omega$	t <sub>R</sub>		2.7		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1.5A, $R_{\text{G(ext)}}$ = 3 $\Omega$	t <sub>D(OFF)</sub>		18.8		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1.5A, $R_{\text{G(ext)}}$ = 3 $\Omega$	t <sub>F</sub>		1.6		ns
Total Gate Charge	$V_{DS}$ = 30V, $V_{GS}$ = 4.5V, $I_D$ = 2.5A	Q <sub>G</sub>		3.6		nC
Gate Source Charge	$V_{DS}$ = 30V, $V_{GS}$ = 4.5V, $I_D$ = 2.5A	Q <sub>GS</sub>		0.8		nC
Gate Drain Charge	$V_{DS}$ = 30V, $V_{GS}$ = 4.5V, $I_{D}$ = 2.5A	$\mathbf{Q}_{GD}$		1.6		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		I <sub>S</sub>			2.5	A
Drain-Source Diode Forward Voltage <sup>Note 3</sup>	$V_{GS} = 0V$ , $I_S = 1A$	$V_{\text{SD}}$			1	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board,  $t \le 10$  sec

3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

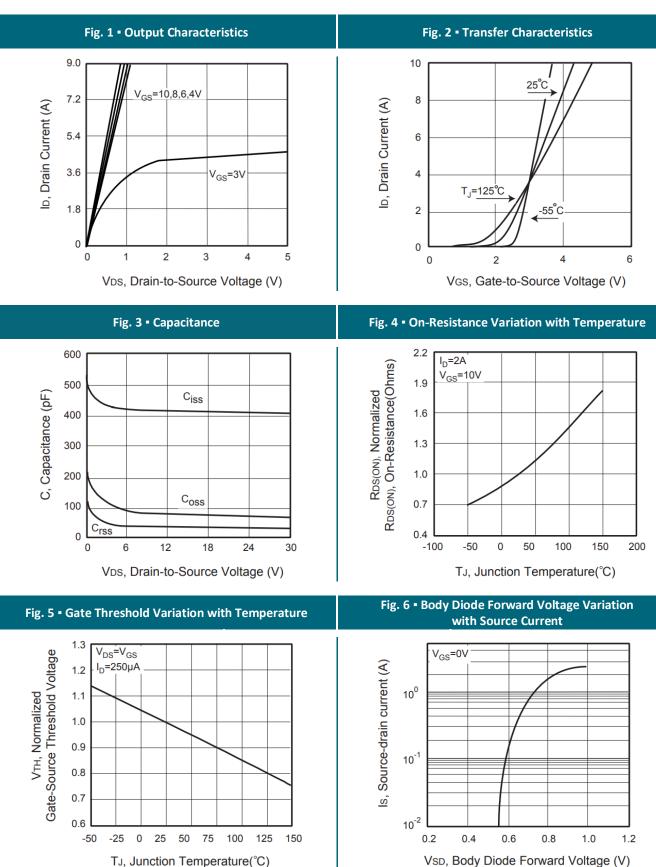
4: Guaranteed by design, not subject to production testing.



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## **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**

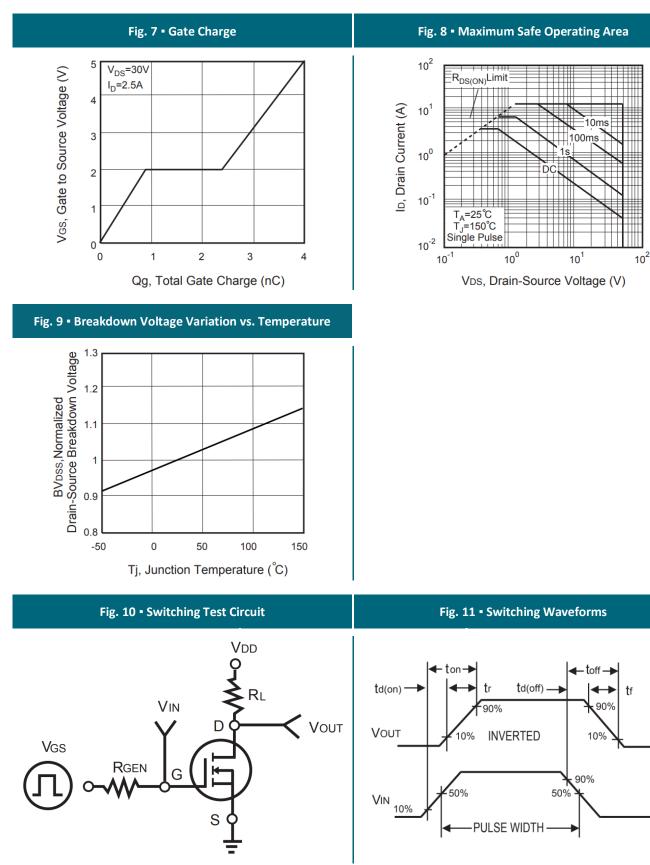


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## **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**



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# **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**

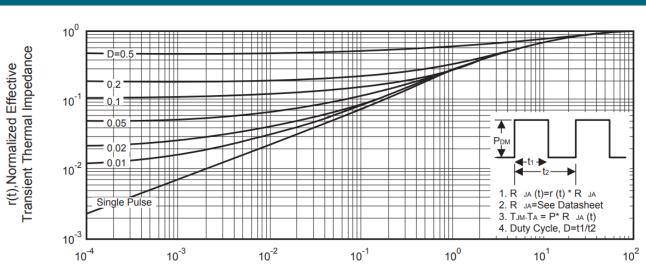
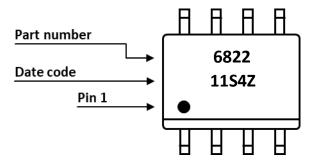


Fig. 12 • Normalized Thermal Transient Impedance Curve

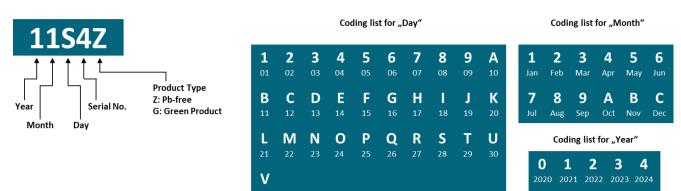
Square Wave Pulse Duration (sec)

## PART MARKING



#### **DATE CODE**

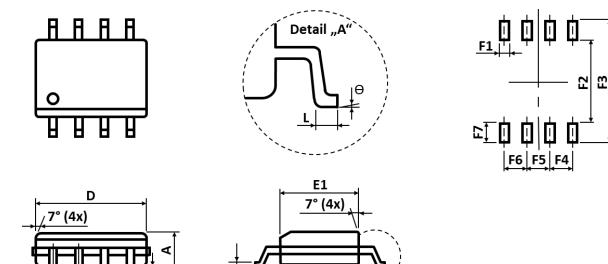
#### Example: 11S4Z



• Detail "A"



## PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	1.350	-	1.750	E1	3.700		4.060
A1	0.100	-	0.250	eB	5.800		6.200
В	0.310	-	0.510	е		1.270	
С	0.170	-	0.250	L	0.400		0.950
D	4.690	-	5.000	θ	0°	-	8°
Sym	Millimeters	Millimeters	Millimeters	Sym	Millimeters	Millimeters	Millimeters

eВ

Sym	(Min.)	(Typ.)	(Max.)	Sym	(Min.)	(Typ.)	(Max.)	
F1	-	0.500	-	F5	-	1.270	-	
F2	-	4.250	-	F6	-	1.270	-	
F3	-	6.250	-	F7	-	1.000	-	
F4	-	1.270	-					

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

C

# **ORDERING INFORMATION**

В

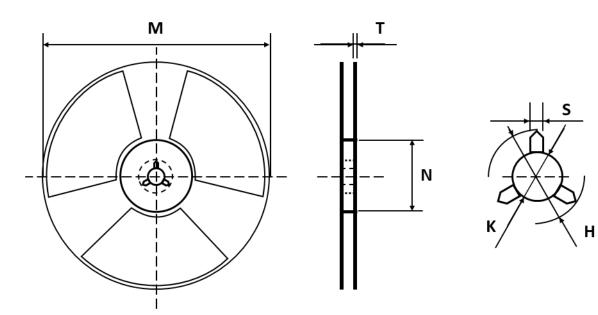
**A1** 

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEM6822	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs



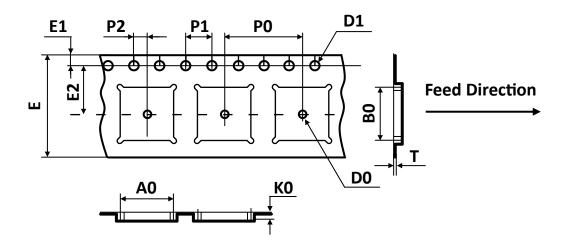


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	Ν	т	Н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	<b>\$550</b>	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

#### **TAPE DIMENSIONS** All dimensions in mm



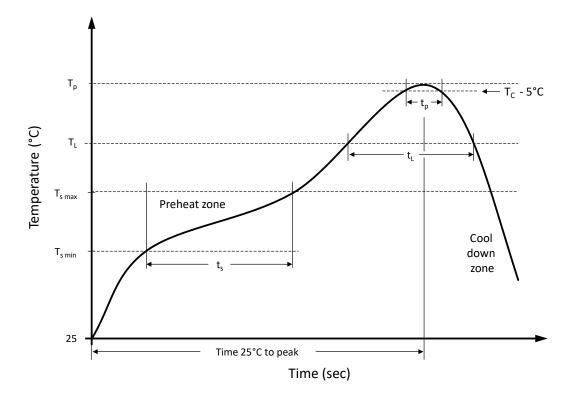
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





## **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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